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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Obsolete
Number of LABs/CLBs	216
Number of Logic Elements/Cells	1728
Total RAM Bits	12288
Number of I/O	147
Number of Gates	69000
Voltage - Supply	4.75V ~ 5.25V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 70°C (TA)
Package / Case	208-BFQFP Exposed Pad
Supplier Device Package	208-RQFP (28x28)
Purchase URL	https://www.e-xfl.com/product-detail/intel/epf10k30rc208-4n

For improved routing, the row interconnect is comprised of a combination of full-length and half-length channels. The full-length channels connect to all LABs in a row; the half-length channels connect to the LABs in half of the row. The EAB can be driven by the half-length channels in the left half of the row and by the full-length channels. The EAB drives out to the full-length channels. In addition to providing a predictable, row-wide interconnect, this architecture provides increased routing resources. Two neighboring LABs can be connected using a half-row channel, thereby saving the other half of the channel for the other half of the row.

Table 7 summarizes the FastTrack Interconnect resources available in each FLEX 10K device.

Table 7. FLEX 10K FastTrack Interconnect Resources				
Device	Rows	Channels per Row	Columns	Channels per Column
EPF10K10 EPF10K10A	3	144	24	24
EPF10K20	6	144	24	24
EPF10K30 EPF10K30A	6	216	36	24
EPF10K40	8	216	36	24
EPF10K50 EPF10K50V	10	216	36	24
EPF10K70	9	312	52	24
EPF10K100 EPF10K100A	12	312	52	24
EPF10K130V	16	312	52	32
EPF10K250A	20	456	76	40

In addition to general-purpose I/O pins, FLEX 10K devices have six dedicated input pins that provide low-skew signal distribution across the device. These six inputs can be used for global clock, clear, preset, and peripheral output enable and clock enable control signals. These signals are available as control signals for all LABs and IOEs in the device.

The dedicated inputs can also be used as general-purpose data inputs because they can feed the local interconnect of each LAB in the device. However, the use of dedicated inputs as data inputs can introduce additional delay into the control signal network.

Figure 13. Bidirectional I/O Registers

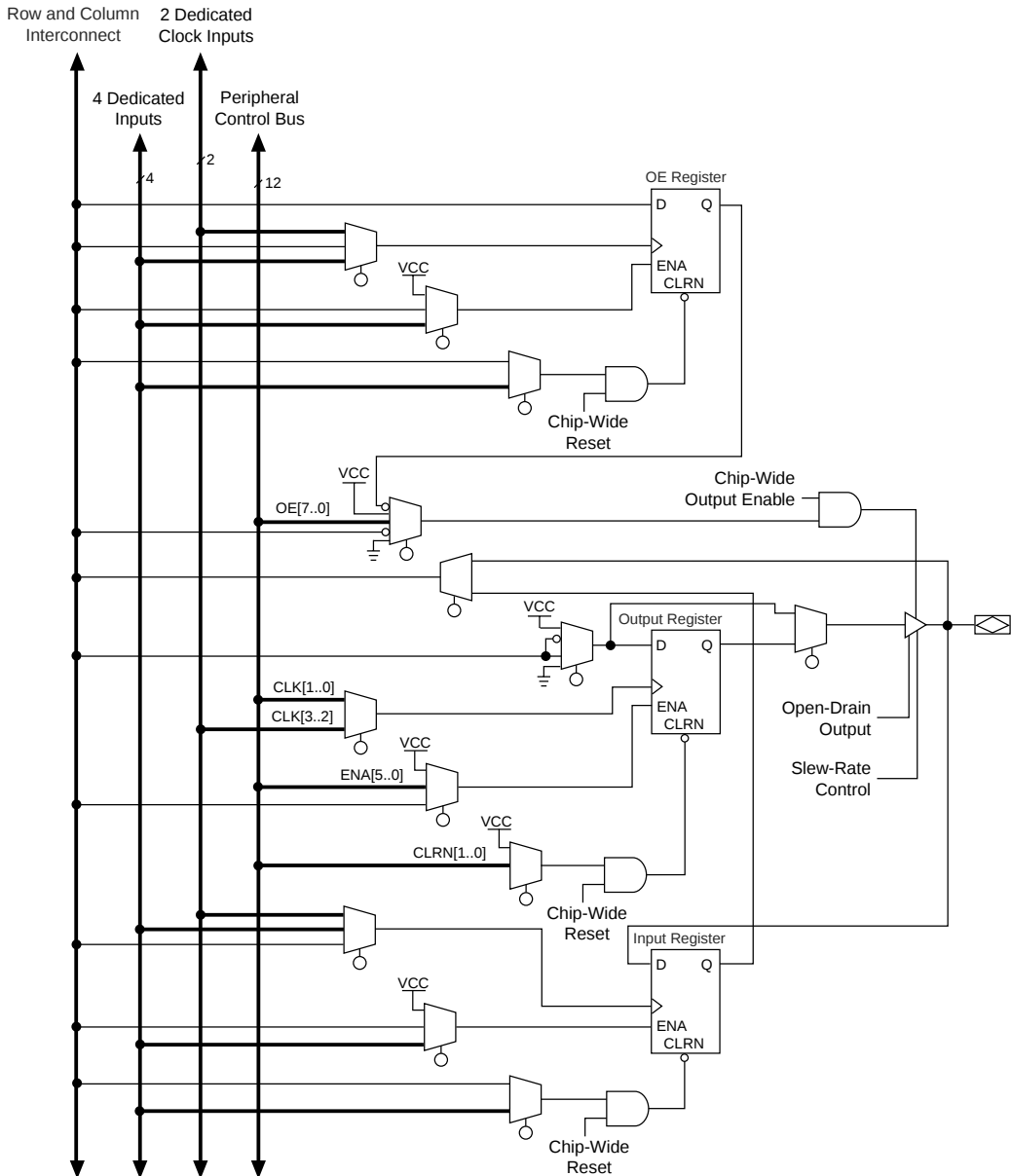


Table 8. EPF10K10, EPF10K20, EPF10K30, EPF10K40 & EPF10K50 Peripheral Bus Sources

Peripheral Control Signal	EPF10K10 EPF10K10A	EPF10K20	EPF10K30 EPF10K30A	EPF10K40	EPF10K50 EPF10K50V
OE0	Row A	Row A	Row A	Row A	Row A
OE1	Row A	Row B	Row B	Row C	Row B
OE2	Row B	Row C	Row C	Row D	Row D
OE3	Row B	Row D	Row D	Row E	Row F
OE4	Row C	Row E	Row E	Row F	Row H
OE5	Row C	Row F	Row F	Row G	Row J
CLKENA0/CLK0/GLOBAL0	Row A	Row A	Row A	Row B	Row A
CLKENA1/OE6/GLOBAL1	Row A	Row B	Row B	Row C	Row C
CLKENA2/CLR0	Row B	Row C	Row C	Row D	Row E
CLKENA3/OE7/GLOBAL2	Row B	Row D	Row D	Row E	Row G
CLKENA4/CLR1	Row C	Row E	Row E	Row F	Row I
CLKENA5/CLK1/GLOBAL3	Row C	Row F	Row F	Row H	Row J

Table 9. EPF10K70, EPF10K100, EPF10K130V & EPF10K250A Peripheral Bus Sources

Peripheral Control Signal	EPF10K70	EPF10K100 EPF10K100A	EPF10K130V	EPF10K250A
OE0	Row A	Row A	Row C	Row E
OE1	Row B	Row C	Row E	Row G
OE2	Row D	Row E	Row G	Row I
OE3	Row I	Row L	Row N	Row P
OE4	Row G	Row I	Row K	Row M
OE5	Row H	Row K	Row M	Row O
CLKENA0/CLK0/GLOBAL0	Row E	Row F	Row H	Row J
CLKENA1/OE6/GLOBAL1	Row C	Row D	Row F	Row H
CLKENA2/CLR0	Row B	Row B	Row D	Row F
CLKENA3/OE7/GLOBAL2	Row F	Row H	Row J	Row L
CLKENA4/CLR1	Row H	Row J	Row L	Row N
CLKENA5/CLK1/GLOBAL3	Row E	Row G	Row I	Row K

Table 13. FLEX 10K JTAG Instructions

JTAG Instruction	Description
SAMPLE/PRELOAD	Allows a snapshot of signals at the device pins to be captured and examined during normal device operation, and permits an initial data pattern output at the device pins.
EXTEST	Allows the external circuitry and board-level interconnections to be tested by forcing a test pattern at the output pins and capturing test results at the input pins.
BYPASS	Places the 1-bit bypass register between the TDI and TDO pins, which allows the BST data to pass synchronously through a selected device to adjacent devices during normal device operation.
USERCODE	Selects the user electronic signature (USERCODE) register and places it between the TDI and TDO pins, allowing the USERCODE to be serially shifted out of TDO
IDCODE	Selects the IDCODE register and places it between TDI and TDO allowing the IDCODE to be serially shifted out of TDO
ICR Instructions	These instructions are used when configuring a FLEX 10K device via JTAG ports with a BitBlaster, or ByteBlasterMV or MasterBlaster download cable, or using a Jam File (.jam) or Jam Byte-Code File (.jbc) via an embedded processor.

The instruction register length of FLEX 10K devices is 10 bits. The USERCODE register length in FLEX 10K devices is 32 bits; 7 bits are determined by the user, and 25 bits are predetermined. Tables 14 and 15 show the boundary-scan register length and device IDCODE information for FLEX 10K devices.

Table 14. FLEX 10K Boundary-Scan Register Length

Device	Boundary-Scan Register Length
EPF10K10, EPF10K10A	480
EPF10K20	624
EPF10K30, EPF10K30A	768
EPF10K40	864
EPF10K50, EPF10K50V	960
EPF10K70	1,104
EPF10K100, EPF10K100A	1,248
EPF10K130V	1,440
EPF10K250A	1,440

Table 15. 32-Bit FLEX 10K Device IDCODE^{Note (1)}

Device	IDCODE (32 Bits)			
	Version (4 Bits)	Part Number (16 Bits)	Manufacturer's Identity (11 Bits)	1 (1 Bit) (2)
EPF10K10, EPF10K10A	0000	0001 0000 0001 0000	00001101110	1
EPF10K20	0000	0001 0000 0010 0000	00001101110	1
EPF10K30, EPF10K30A	0000	0001 0000 0011 0000	00001101110	1
EPF10K40	0000	0001 0000 0100 0000	00001101110	1
EPF10K50, EPF10K50V	0000	0001 0000 0101 0000	00001101110	1
EPF10K70	0000	0001 0000 0111 0000	00001101110	1
EPF10K100, EPF10K100A	0000	0000 0001 0000 0000	00001101110	1
EPF10K130V	0000	0000 0001 0011 0000	00001101110	1
EPF10K250A	0000	0000 0010 0101 0000	00001101110	1

Notes:

- (1) The most significant bit (MSB) is on the left.
 (2) The least significant bit (LSB) for all JTAG IDCODEs is 1.

FLEX 10K devices include weak pull-ups on JTAG pins.

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For more information, see the following documents:

Application Note 39 (IEEE 1149.1 (JTAG) Boundary-Scan Testing in Altera Devices)

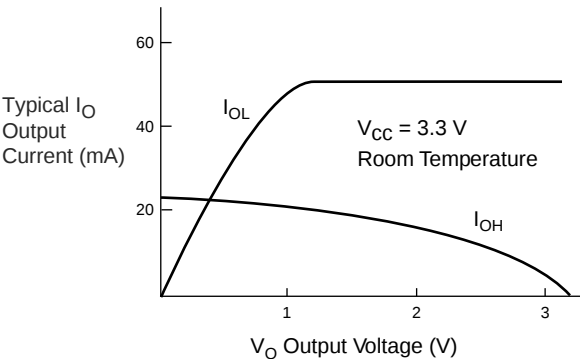
BitBlaster Serial Download Cable Data Sheet

ByteBlasterMV Parallel Port Download Cable Data Sheet

Jam Programming & Test Language Specification

Figure 21 shows the typical output drive characteristics of EPF10K50V and EPF10K130V devices.

Figure 21. Output Drive Characteristics of EPF10K50V & EPF10K130V Devices



Tables 26 through 31 provide information on absolute maximum ratings, recommended operating conditions, DC operating conditions, and capacitance for 3.3-V FLEX 10K devices.

Table 26. FLEX 10KA 3.3-V Device Absolute Maximum Ratings ^{Note (1)}					
Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	Supply voltage	With respect to ground (2)	≥ 0.5	4.6	V
V_I	DC input voltage		≥ 2.0	5.75	V
I_{OUT}	DC output current, per pin		≥ 25	25	mA
T_{STG}	Storage temperature	No bias	≥ 65	150	$^{\circ}$ C
T_{AMB}	Ambient temperature	Under bias	≥ 65	135	$^{\circ}$ C
T_J	Junction temperature	Ceramic packages, under bias		150	$^{\circ}$ C
		PQFP, TQFP, RQFP, and BGA packages, under bias		135	$^{\circ}$ C

Figure 26. FLEX 10K Device IOE Timing Model

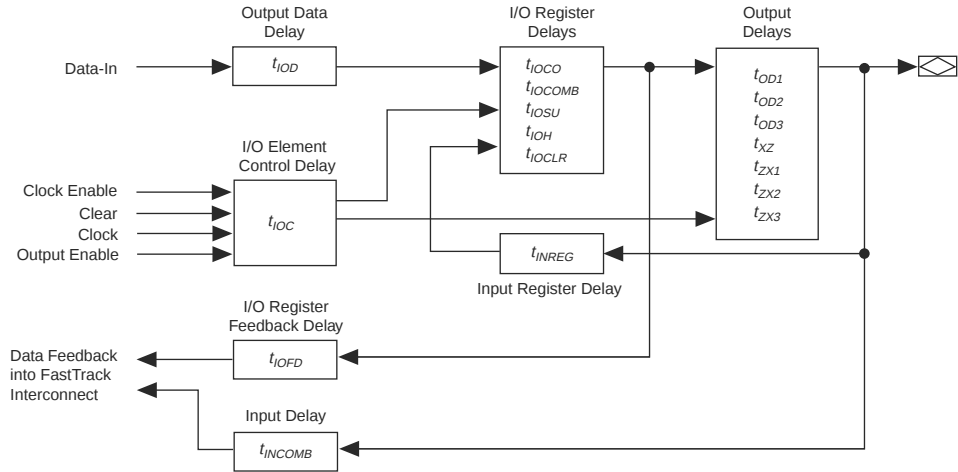


Figure 27. FLEX 10K Device EAB Timing Model

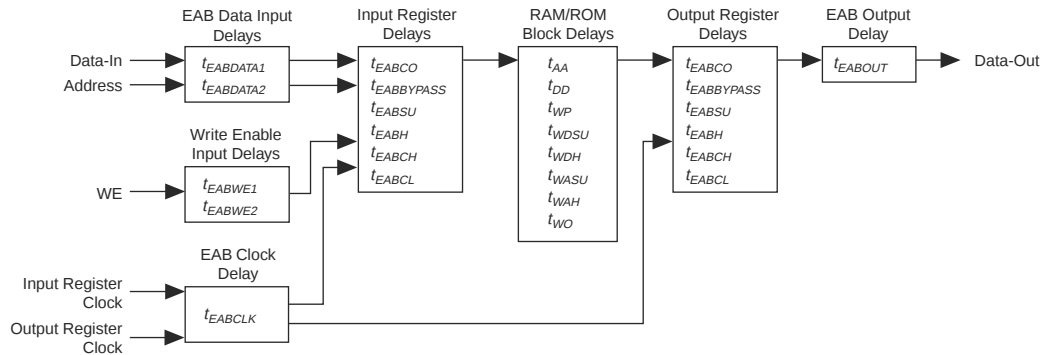


Figure 28 shows the timing model for bidirectional I/O pin timing.

Table 34. EAB Timing Microparameters Note (1)

Symbol	Parameter	Conditions
t_{EABDATA1}	Data or address delay to EAB for combinatorial input	
t_{EABDATA2}	Data or address delay to EAB for registered input	
t_{EABWE1}	Write enable delay to EAB for combinatorial input	
t_{EABWE2}	Write enable delay to EAB for registered input	
t_{EABCLK}	EAB register clock delay	
t_{EABCO}	EAB register clock-to-output delay	
t_{EABYPASS}	Bypass register delay	
t_{EABSU}	EAB register setup time before clock	
t_{EABH}	EAB register hold time after clock	
t_{AA}	Address access delay	
t_{WP}	Write pulse width	
t_{WDSU}	Data setup time before falling edge of write pulse	(5)
t_{WDH}	Data hold time after falling edge of write pulse	(5)
t_{WASU}	Address setup time before rising edge of write pulse	(5)
t_{WAH}	Address hold time after falling edge of write pulse	(5)
t_{WO}	Write enable to data output valid delay	
t_{DD}	Data-in to data-out valid delay	
t_{EABOUT}	Data-out delay	
t_{EABCH}	Clock high time	
t_{EABCL}	Clock low time	

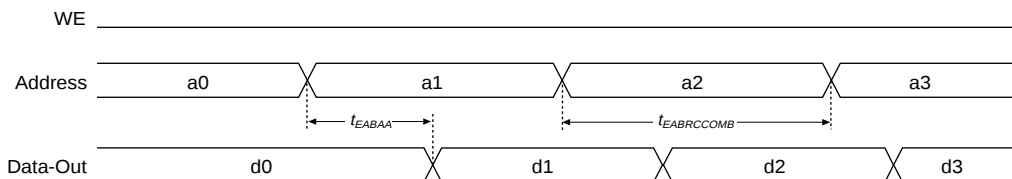
Notes to tables:

- (1) Microparameters are timing delays contributed by individual architectural elements. These parameters cannot be measured explicitly.
- (2) Operating conditions: $V_{CCIO} = 5.0\text{ V} \pm 5\%$ for commercial use in FLEX 10K devices.
 $V_{CCIO} = 5.0\text{ V} \pm 10\%$ for industrial use in FLEX 10K devices.
 $V_{CCIO} = 3.3\text{ V} \pm 10\%$ for commercial or industrial use in FLEX 10KA devices.
- (3) Operating conditions: $V_{CCIO} = 3.3\text{ V} \pm 10\%$ for commercial or industrial use in FLEX 10K devices.
 $V_{CCIO} = 2.5\text{ V} \pm 0.2\text{ V}$ for commercial or industrial use in FLEX 10KA devices.
- (4) Operating conditions: $V_{CCIO} = 2.5\text{ V}, 3.3\text{ V}, \text{ or } 5.0\text{ V}$.
- (5) Because the RAM in the EAB is self-timed, this parameter can be ignored when the WE signal is registered.
- (6) EAB macroparameters are internal parameters that can simplify predicting the behavior of an EAB at its boundary; these parameters are calculated by summing selected microparameters.
- (7) These parameters are worst-case values for typical applications. Post-compilation timing simulation and timing analysis are required to determine actual worst-case performance.
- (8) External reference timing parameters are factory-tested, worst-case values specified by Altera. A representative subset of signal paths is tested to approximate typical device applications.
- (9) Contact Altera Applications for test circuit specifications and test conditions.
- (10) These timing parameters are sample-tested only.

Figures 29 and 30 show the asynchronous and synchronous timing waveforms, respectively, for the EAB macroparameters in Table 34

Figure 29. EAB Asynchronous Timing Waveforms

EAB Asynchronous Read



EAB Asynchronous Write

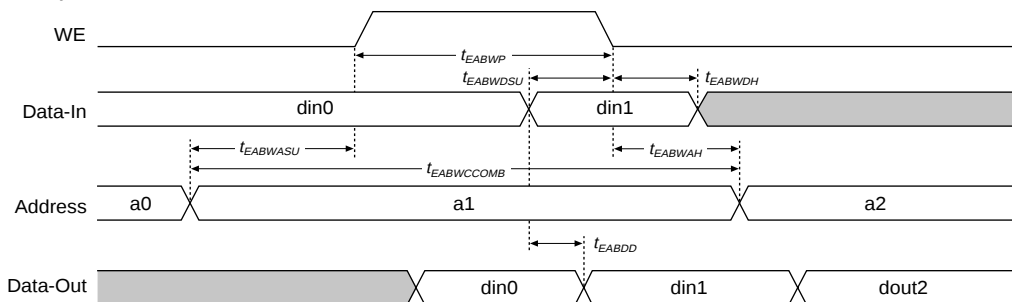


Table 40. EPF10K10 & EPF10K20 Device IOE Timing Microparameters ^{Note (1)}

Symbol	-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	
t_{IOD}		1.3		1.6	ns
t_{IOC}		0.5		0.7	ns
t_{ICO}		0.2		0.2	ns
t_{IOCOMB}		0.0		0.0	ns
t_{IOSU}	2.8		3.2		ns
t_{IOH}	1.0		1.2		ns
t_{IOCLR}		1.0		1.2	ns
t_{OD1}		2.6		3.5	ns
t_{OD2}		4.9		6.4	ns
t_{OD3}		6.3		8.2	ns
t_{XZ}		4.5		5.4	ns
t_{ZX1}		4.5		5.4	ns
t_{ZX2}		6.8		8.3	ns
t_{ZX3}		8.2		10.1	ns
t_{INREG}		6.0		7.5	ns
t_{IOFD}		3.1		3.5	ns
t_{INCOMB}		3.1		3.5	ns

Table 51. EPF10K30, EPF10K40 & EPF10K50 Device EAB Internal Timing Macroparameters (1)

Symbol	-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	
t_{EABAA}		13.7		17.0	ns
$t_{EABRCCOMB}$	13.7		17.0		ns
$t_{EABRCREG}$	9.7		11.9		ns
t_{EABWP}	5.8		7.2		ns
$t_{EABWCCOMB}$	7.3		9.0		ns
$t_{EABWCREG}$	13.0		16.0		ns
t_{EABDD}		10.0		12.5	ns
$t_{EABDATA CO}$		2.0		3.4	ns
$t_{EABDATASU}$	5.3		5.6		ns
$t_{EABDATAH}$	0.0		0.0		ns
$t_{EABWESU}$	5.5		5.8		ns
t_{EABWEH}	0.0		0.0		ns
$t_{EABWDSU}$	5.5		5.8		ns
t_{EABWDH}	0.0		0.0		ns
$t_{EABWASU}$	2.1		2.7		ns
t_{EABWAH}	0.0		0.0		ns
t_{EABWO}		9.5		11.8	ns

Table 52. EPF10K30 Device Interconnect Timing Microparameters^{Note (1)}

Symbol	-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	
$t_{DIN2IOE}$		6.9		8.7	ns
t_{DIN2LE}		3.6		4.8	ns
$t_{DIN2DATA}$		5.5		7.2	ns
$t_{DCLK2IOE}$		4.6		6.2	ns
$t_{DCLK2LE}$		3.6		4.8	ns
$t_{SAMELAB}$		0.3		0.3	ns
$t_{SAMEROW}$		3.3		3.7	ns
$t_{SAMECOLUMN}$		2.5		2.7	ns
$t_{DIFFROW}$		5.8		6.4	ns
$t_{TROWROWS}$		9.1		10.1	ns
$t_{LEPERIPH}$		6.2		7.1	ns
$t_{LABCARRY}$		0.4		0.6	ns
$t_{LABCASC}$		2.4		3.0	ns

Table 53. EPF10K40 Device Interconnect Timing Microparameters^{Note (1)}

Symbol	-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	
$t_{DIN2IOE}$		7.6		9.4	ns
t_{DIN2LE}		3.6		4.8	ns
$t_{DIN2DATA}$		5.5		7.2	ns
$t_{DCLK2IOE}$		4.6		6.2	ns
$t_{DCLK2LE}$		3.6		4.8	ns
$t_{SAMELAB}$		0.3		0.3	ns
$t_{SAMEROW}$		3.3		3.7	ns
$t_{SAMECOLUMN}$		3.1		3.2	ns
$t_{DIFFROW}$		6.4		6.4	ns
$t_{TROWROWS}$		9.7		10.6	ns
$t_{LEPERIPH}$		6.4		7.1	ns
$t_{LABCARRY}$		0.4		0.6	ns
$t_{LABCASC}$		2.4		3.0	ns

Table 67. EPF10K100 Device EAB Internal Timing Macroparameters Note (1)

Symbol	-3DX Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{EABAA}		13.7		13.7		17.0	ns
$t_{EABRCCOMB}$	13.7		13.7		17.0		ns
$t_{EABRCREG}$	9.7		9.7		11.9		ns
t_{EABWP}	5.8		5.8		7.2		ns
$t_{EABWCCOMB}$	7.3		7.3		9.0		ns
$t_{EABWCREG}$	13.0		13.0		16.0		ns
t_{EABDD}		10.0		10.0		12.5	ns
$t_{EABDATA CO}$		2.0		2.0		3.4	ns
$t_{EABDATASU}$	5.3		5.3		5.6		ns
$t_{EABDATAH}$	0.0		0.0		0.0		ns
$t_{EABWESU}$	5.5		5.5		5.8		ns
t_{EABWEH}	0.0		0.0		0.0		ns
$t_{EABWDSU}$	5.5		5.5		5.8		ns
t_{EABWDH}	0.0		0.0		0.0		ns
$t_{EABWASU}$	2.1		2.1		2.7		ns
t_{EABWAH}	0.0		0.0		0.0		ns
t_{EABWO}		9.5		9.5		11.8	ns

Table 69. EPF10K100 Device External Timing Parameters^{Note (1)}

Symbol	-3DX Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{DDR}		19.1		19.1		24.2	ns
t_{INSU} (2), (3), (4)	7.8		7.8		8.5		ns
t_{OUTCO} (3), (4)	2.0	11.1	2.0	11.1	2.0	14.3	ns
t_{INH} (3)	0.0		0.0		0.0		ns
t_{INSU} (2), (3), (5)	6.2		∅		∅		ns
t_{OUTCO} (3), (5)	2.0	6.7		∅		∅	ns

Table 70. EPF10K100 Device External Bidirectional Timing Parameters^{Note (1)}

Symbol	-3DX Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{\text{INSUBIDIR}}$ (4)	8.1		8.1		10.4		ns
t_{INHBIDIR} (4)	0.0		0.0		0.0		ns
$t_{\text{OUTCOBIDIR}}$ (4)	2.0	11.1	2.0	11.1	2.0	14.3	ns
t_{XZBIDIR} (4)		15.3		15.3		18.4	ns
t_{ZXBIDIR} (4)		15.3		15.3		18.4	ns
$t_{\text{INSUBIDIR}}$ (5)	9.1		∅		∅		ns
t_{INHBIDIR} (5)	0.0		∅		∅		ns
$t_{\text{OUTCOBIDIR}}$ (5)	2.0	7.2	∅	∅	∅	∅	ns
t_{XZBIDIR} (5)		14.3		∅		∅	ns
t_{ZXBIDIR} (5)		14.3		∅		∅	ns

Notes to tables:

- (1) All timing parameters are described in Tables 32 through 38 in this data sheet.
- (2) Using an LE to register the signal may provide a lower setup time.
- (3) This parameter is specified by characterization.
- (4) This parameter is measured without the use of the ClockLock or ClockBoost circuits.
- (5) This parameter is measured with the use of the ClockLock or ClockBoost circuits.

Table 72. EPF10K50V Device IOE Timing Microparameters Note (1)

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	Min	Max	
t _{IOD}		1.2		1.6		1.9		2.1	ns
t _{IOC}		0.3		0.4		0.5		0.5	ns
t _{IOCO}		0.3		0.3		0.4		0.4	ns
t _{IOCOMB}		0.0		0.0		0.0		0.0	ns
t _{IOSU}	2.8		2.8		3.4		3.9		ns
t _{IOH}	0.7		0.8		1.0		1.4		ns
t _{IOCLR}		0.5		0.6		0.7		0.7	ns
t _{OD1}		2.8		3.2		3.9		4.7	ns
t _{OD2}		Ø		Ø		Ø		Ø	ns
t _{OD3}		6.5		6.9		7.6		8.4	ns
t _{XZ}		2.8		3.1		3.8		4.6	ns
t _{ZX1}		2.8		3.1		3.8		4.6	ns
t _{ZX2}		Ø		Ø		Ø		Ø	ns
t _{ZX3}		6.5		6.8		7.5		8.3	ns
t _{INREG}		5.0		5.7		7.0		9.0	ns
t _{IOFD}		1.5		1.9		2.3		2.7	ns
t _{INCOMB}		1.5		1.9		2.3		2.7	ns

